



SLLS984D -JUNE 2009-REVISED JULY 2010

Low-Power Dual Digital Isolators

Check for Samples: ISO7420, ISO7420M, ISO7421, ISO7421M

FEATURES

- Highest Signaling Rate: 1 Mbps
- Low Power Consumption, Typical I_{CC} per Channel (3.3V operation):
 - ISO7420: 1.1 mA, ISO7421: 1.5 mA
- Low Propagation Delay 9 ns Typ. and Low Skew – 300 ps Typ.
- Wide T_A Range Specified: -40°C to 125°C
- 4-kVpeak Maximum Isolation, 2.5 kVrms per UL 1577, IEC/VDE and CSA Approvals, IEC 60950-1, IEC 61010-1 End Equipment Standards Approvals. All Approvals Pending.
- 50 kV/μs Transient Immunity, Typical
- Over 25-Year Isolation Integrity at Rated Voltage
- Operates From 3.3V and 5V Supply and Logic Levels

APPLICATIONS

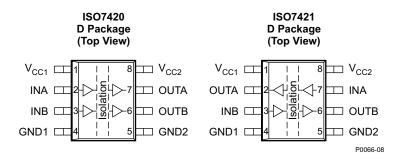
- Optocoupler Replacement in:
 - Industrial Fieldbus
 - Profibus
 - Modbus
 - DeviceNet™ Data Buses
 - Servo Control Interface
 - Motor Control
 - Power Supplies
 - Battery Packs

DESCRIPTION

The ISO7420, ISO7420M, ISO7421, and ISO7421M provide galvanic isolation up to 2.5 kVrms for 1 minute per UL. These digital isolators have two isolated channels. Each isolation channel has a logic input and output buffer separated by a silicon dioxide (SiO₂) insulation barrier. Used in conjunction with isolated power supplies, these devices prevent noise currents on a data bus or other circuit from entering the local ground and interfering with or damaging sensitive circuitry. The suffix M indicates wide temperature range (–40°C to 125°C).

The devices have TTL input thresholds and require two supply voltages, 3.3V or 5V, or any combination. All inputs are 5-V tolerant when supplied from a 3.3V supply.

Note: The ISO7420 and ISO7421 are specified for signaling rates up to 1 Mbps. Due to their fast response time, under most cases, these devices will also transmit data with much shorter pulse widths. Designers should add external filtering to remove spurious signals with input pulse duration < 20ns if desired.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

PIN FUNCTIONS

	PIN		DESCRIPTION	
NAME	NO.	I/O	DESCRIPTION	
INA	7	I	Input, channel A	
INB	3	1	Input, channel B	
GND1	4	_	Ground connection for V _{CC1}	
GND2	5	_	Ground connection for V _{CC2}	
OUTA	2	0	Output, channel A	
OUTB	6	0	Output, channel B	
V _{CC1}	1	_	Power supply, V _{CC1}	
V _{CC2}	8	_	Power supply, V _{CC2}	

Table 1. FUNCTION TABLE(1)

INPUT SIDE VCC	OUTPUT SIDE VCC	INPUT IN	OUTPUT OUT
		Н	Н
PU	PU	L	L
		Open	H ⁽²⁾
PD	PU	Х	H ⁽²⁾

- (1) PU = Powered up ($V_{CC} \ge 3$ V); PD = Powered down ($V_{CC} \le 2.4$ V); X = Irrelevant; H = High level; L = Low level
- (2) In fail-safe condition, output is at high level for ISO7420, ISO7420M, ISO7421 and ISO7421M.

AVAILABLE OPTIONS

PRODUCT	RATED ISOLATION	PACKAGE	INPUT THRESHOLD	RATED T _A	CHANNEL DIRECTION	MARKED AS	ORDERING NUMBER						
ISO7420				–40°C to 105°C		IS7420	ISO7420D (rail)						
1307420				-40 C to 105 C		137420	ISO7420DR (reel)						
				-40°C to 125°C							Same direction		ISO7420MD (rail)
ISO7420M	2.5 kVrms	D-8	~1.5 V (TTL)			17420M	ISO7420MDR (reel)						
ISO7421	2.5 KVIIIIS	D-6	(CMOS compatible)	40°C to 405°C		107404	ISO7421D (rail)						
1507421				–40°C to 105°C	Onnosito	IS7421	ISO7421DR (reel)						
ISO7421M					Opposite directions		ISO7421MD (rail)						
(PREVIEW)				–40°C to 125°C		17421M	ISO7421MDR (reel)						

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ABSOLUTE MAXIMUM RATINGS(1)

					VALUE		
V_{CC}	Supply voltage ⁽	²⁾ , V _{CC1} , V _{CC2}			–0.5 V to 6 V		
V_{I}	Voltage at IN, OUT						
lo	Output current				±15 mA		
	Electrostatic discharge	Human-body model	JEDEC Standard 22, Test Method A114-C.01		±4 kV		
ESD		Field-induced charged-device model	JEDEC Standard 22, Test Method C101	All pins	±1.5 kV		
		Machine model	ANSI/ESDS5.2-1996		±200 V		
T _{J(Max)}	lax) Maximum junction temperature						
T _{stg}	Storage temper	Storage temperature					

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

		MIN	TYP	MAX	UNIT
V _{CC1} , V _{CC2}	Supply voltage - 3.3V operation	3.15	3.3	3.45	V
	Supply voltage - 5V operation	4.75	5	5.25	
I _{OH}	High-level output current	-4			mA
I _{OL}	Low-level output current			4	mA
V _{IH}	High-level input voltage	2		V_{CC}	V
V _{IL}	Low-level input voltage	0		0.8	V
$T_{J}^{(1)}$	Junction temperature	-40		136	°C
1/t _{ui}	Signaling rate	0		1	Mbps
t _{ui}	Input pulse duration	1			us

To maintain the recommended operating conditions for T_J, see the Package Thermal Characteristics table and the I_{CC} limits in this data sheet.

⁽²⁾ All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values.



 V_{CC1} and V_{CC2} at 5V \pm 5%; $T_A = -40^{\circ}$ C to 125°C for ISO742xM, $T_A = -40^{\circ}$ C to 105°C for ISO742x

	PARAMETER	7	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V	Lligh level output voltage	$I_{OH} = -4$ mA; see Figure 1.		$V_{CC} - 0.8$	4.6		V
V _{OH}	High-level output voltage	$I_{OH} = -20 \mu A;$	see Figure 1.	V _{CC} - 0.1	5		V
V	Landard and and and and	$I_{OL} = 4 \text{ mA}$; se	e Figure 1.		0.2	0.4	
V_{OL}	Low-level output voltage	$I_{OL} = 20 \mu A; see$	ee Figure 1.	10 μA -10 μA 25 50 kV/μ	V		
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	INT1 0 1/1	,			10	μА
I _{IL}	Low-level input current	INx at 0 V or V	cc c	-10			μА
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 \	$V_I = V_{CC}$ or 0 V; see Figure 3.		50		kV/μs
SUPPL	Y CURRENT (All inputs switching w	ith square way	e clock signal for dynamic ICC	measurement)			
	ISO7420						
I _{CC1}	Supply current for V _{CC1}	DO (- 4 M)	V V 0 V 45 - 5 land		0.4	1	
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		3	6	mA
	ISO7421	•	,			ļ.	
I _{CC1}	Supply current for V _{CC1}	DC to 4 Mb = -	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		2	4	mA
I _{CC2}	Supply current for V _{CC2}	TOC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		2	4	

SWITCHING CHARACTERISTICS

 V_{CC1} and V_{CC2} at 5V \pm 5%; $T_A = -40^{\circ}C$ to 125°C for ISO742xM, $T_A = -40^{\circ}C$ to 105°C for ISO742X

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1.		9	14	ns
PWD ⁽¹⁾	Pulse width distortion t _{PHL} - t _{PLH}			0.3	3.5	ns
t _{sk(pp)}	Part-to-part skew time				4	ns
t _{sk(o)}	Channel-to-channel output skew time				3.6	ns
t _r	Output signal rise time	See Figure 1.		1		ns
t _f	Output signal fall time			1		ns
t _{fs}	Fail-safe output delay time from input power loss	See Figure 2.		6		μS

⁽¹⁾ Also known as pulse skew.



 V_{CC1} at 5V ± 5%, V_{CC2} at 3.3V ± 5%; T_A = -40°C to 125°C for ISO742xM , T_A = -40°C to 105°C for ISO742x

	PARAMETER	TE	EST CONDITIONS	MIN	TYP	MAX	UNIT
		$I_{OH} = -4 \text{ mA};$	ISO7421 (5-V side)	V _{CC} - 0.8	4.6		
V_{OH}	High-level output voltage	see Figure 1.	ISO7420 / 7421 (3.3-V side)	V _{CC} - 0.4	3		V
		$I_{OH} = -20 \mu A;$	see Figure 1,	V _{CC} - 0.1	V _{CC}		
	Law law law taut with an	I _{OL} = 4 mA; see Figure 1.			0.2	0.4	V
V_{OL}	Low-level output voltage	I _{OL} = 20 μA; see Figure 1.			0	0.1	V
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	INIcode O.V. cm.V.				10	μΑ
I _{IL}	Low-level input current	INx at 0 V or \	CC	-10			μΑ
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0	V; see Figure 3.	25	40		kV/μs
SUPPLY	CURRENT (All inputs switching with	square wave clo	ck signal for dynamic ICC me	asurement)			
	ISO7420						
I _{CC1}	Supply current for V _{CC1}	DC to 1 Mbno	\\ \\ or 0 \\ 45 pF lood		0.4	1	mA
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		2	4.5	mA
	ISO7421						
I _{CC1}	Supply current for V _{CC1}	DC to 1 Mbno	\\ \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		2	4	mA
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		1.5	3.5	mA

SWITCHING CHARACTERISTICS

 V_{CC1} at 5V ± 5%, V_{CC2} at 3.3V ± 5%; $T_A = -40^{\circ}C$ to 125°C for ISO742xM, $T_A = -40^{\circ}C$ to 105°C for ISO742x

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1.		10	17	ns
PWD ⁽¹⁾	Pulse width distortion t _{PHL} - t _{PLH}			0.5	4	ns
t _{sk(pp)}	Part-to-part skew time				5	ns
t _{sk(o)}	Channel-to-channel output skew time				4	ns
t _r	Output signal rise time	See Figure 1.		2		ns
t _f	Output signal fall time			2		ns
t _{fS}	Fail-safe output delay time from input power loss	See Figure 2.		6		μS

⁽¹⁾ Also known as pulse skew.



 V_{CC1} at 3.3V ± 5%, V_{CC2} at 5V ± 5%; $T_A = -40$ °C to 125°C for ISO742xM, $T_A = -40$ °C to 105°C for ISO742X

	PARAMETER	TE	ST CONDITIONS	MIN	TYP	MAX	UNIT	
		I _{OH} = -4 mA; see Figure 1.	ISO7420 / 7421 (5-V side).	V _{CC} - 0.8	4.6			
V_{OH}	High-level output voltage		ISO7421 (3.3-V side)	$V_{CC} - 0.4$	3		V	
		$I_{OH} = -20 \mu A; s$	ee Figure 1	V _{CC} - 0.1	V _{CC}			
\ <i>/</i>	Lavidaval avitavit valtava	I _{OL} = 4 mA; see	Figure 1.		0.2	0.4		
V_{OL}	Low-level output voltage	$I_{OL} = 20 \mu A$; se	e Figure 1.		0	4.6 3 V _{CC} 0.2 0.4	V	
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV	
I _{IH}	High-level input current	INIv et 0 V er V	III. (OV.)			10	μΑ	
I _{IL}	Low-level input current	INx at 0 V or V	CC	-10			μΑ	
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V	; see Figure 3.	25	40		kV/μs	
SUPPLY	CURRENT (All inputs switching with	square wave cloc	k signal for dynamic ICC me	asurement)				
	ISO7420							
I _{CC1}	Supply current for V _{CC1}	DC to 4 Mbns	\\ \\ a=0\\ 45 =5 land		0.2	0.7	A	
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		3	6	mA	
	ISO7421							
I _{CC1}	Supply current for V _{CC1}	DC to 1 Mbno	\/ \/ or 0 \/ 15 pF lood		1.5	3.5	mA	
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		2	4		

SWITCHING CHARACTERISTICS

 V_{CC1} at 3.3V ± 5%, V_{CC2} at 5V ± 5%, $T_A = -40$ °C to 125°C for ISO742xM, $T_A = -40$ °C to 105°C for ISO742x

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time	See Figure 1.		10	17	ns
PWD ⁽¹⁾	Pulse width distortion t _{PHL} - t _{PLH}			0.5	4	ns
t _{sk(pp)}	Part-to-part skew time				5	ns
t _{sk(o)}	Channel-to-channel output skew time				4	ns
t _r	Output signal rise time	See Figure 1.		2		ns
t _f	Output signal fall time			2		ns
t _{fS}	Fail-safe output delay time from input power loss	See Figure 2.		6		μS

⁽¹⁾ Also known as pulse skew.



 V_{CC1} and V_{CC2} at 3.3V \pm 5%, T_A = -40°C to 125°C for ISO742xM, T_A = -40°C to 105°C for ISO742x

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V	Lligh level cutout valtage	$I_{OH} = -4 \text{ mA}$; se	ee Figure 1.	$V_{CC} - 0.4$	3		V
V_{OH}	High-level output voltage	$I_{OH} = -20 \mu A; s$	ee Figure 1.	V _{CC} - 0.1	3.3		V
.,	Landard autoritari	I _{OL} = 4 mA; see	Figure 1.		0.2	0.4	
V _{OL}	Low-level output voltage	$I_{OL} = 20 \mu A; see$	e Figure 1.		0	0.1	V
V _{I(HYS)}	Input threshold voltage hysteresis				400		mV
I _{IH}	High-level input current	IN to 24 0 1/2 22 1/2				10	μА
I _{IL}	Low-level input current	INx at 0 V or V ₀	CC .	-10			μА
CMTI	Common-mode transient immunity	$V_I = V_{CC}$ or 0 V	; see Figure 3.	25	40		kV/μs
SUPPL	Y CURRENT (All inputs switching	with square wa	ave clock signal for dynamic ICC	measurement)			
	ISO7420						
I _{CC1}	Supply current for V _{CC1}	20 / 114			0.2	0.7	
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		2	4.5	mA
	ISO7421					•	
I _{CC1}	Supply current for V _{CC1}	DO to 4 Minor	V V == 0.V 45 = 5 land		1.5	3.5	A
I _{CC2}	Supply current for V _{CC2}	DC to 1 Mbps	$V_I = V_{CC}$ or 0 V, 15 pF load		1.5	3.5	mA

SWITCHING CHARACTERISTICS

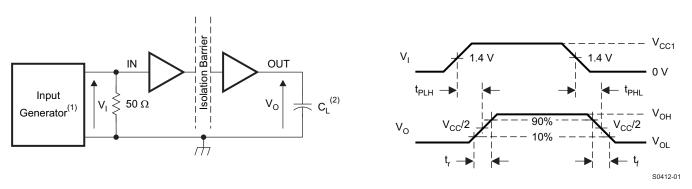
 V_{CC1} and V_{CC2} at 3.3V \pm 5%, T_A = -40°C to 125°C for ISO742xM, T_A = -40°C to 105°C for ISO742x

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay time			12	20	ns
PWD ⁽¹⁾	Pulse width distortion t _{PHL} - t _{PLH}	See Figure 1.		1	5	ns
t _{sk(pp)}	Part-to-part skew time				6	ns
t _{sk(o)}	Channel-to-channel output skew time				5.5	ns
t _r	Output signal rise time	Coo Figure 1		2		ns
t _f	Output signal fall time	See Figure 1.		2		ns
t _{fs}	Fail-safe output delay time from input power loss	See Figure 2.		6		μS

⁽¹⁾ Also known as pulse skew.

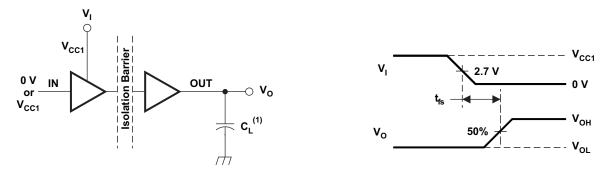


PARAMETER MEASUREMENT INFORMATION



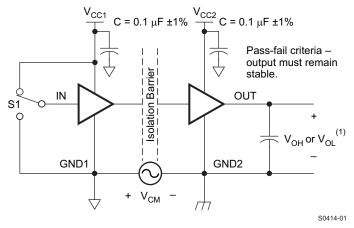
- (1) The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50 \Omega$. At the input, a 50- Ω resistor is required to terminate the Input Generator signal. It is not needed in an actual application.
- (2) $C_L = 15 \text{ pF} \pm 20\%$ includes instrumentation and fixture capacitance.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms



(1) $C_L = 15 \text{ pF} \pm 20\%$ includes instrumentation and fixture capacitance.

Figure 2. Fail-Safe Output Delay-Time Test Circuit and Voltage Waveforms



(1) $C_L = 15 \text{ pF} \pm 20\%$ includes instrumentation and fixture capacitance.

Figure 3. Common-Mode Transient Immunity Test Circuit



DEVICE INFORMATION

PACKAGE CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	4.8			mm
L(102)	Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	4.3			mm
СТІ	Tracking resistance (comparative tracking index)	DIN IEC 60112 / VDE 0303 Part 1	>175			V
	Minimum internal gap (internal clearance)	Distance through the insulation	0.014			mm
Б	Isolation resistance, input to	V _{IO} = 500 V, T _A < 100°C		>10 ¹²		Ω
R _{IO}	output ⁽¹⁾	$V_{IO} = 500 \text{ V}, 100^{\circ}\text{C} \le T_{A} \le \text{max}$		>10 ¹¹		Ω
C _{IO}	Barrier capacitance, input to output ⁽¹⁾	V _{IO} = 0.4 sin (2πft), f = 1 MHz		1		pF
C _I	Input capacitance ⁽²⁾	$V_I = V_{CC}/2 + 0.4 \sin(2\pi ft), f = 1 \text{ MHz}, V_{CC} = 5 \text{ V}$		1		pF

⁽¹⁾ All pins on each side of the barrier tied together creating a two-terminal device.

NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

INSULATION CHARACTERISTICS(3)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	SPECIFICATION	UNIT
V_{IORM}	Maximum working insulation voltage		560	Vpeak
V_{PR}	Input-to-output test voltage	t = 1 s (100% production), partial discharge 5 pC	1050	Vpeak
V	Transient eventeltere	t = 60 s (qualification)	4000	Vpeak
V_{IOTM}	Transient overvoltage	t = 1 s (100% production)	4000	
	Isolation voltage per UL	t = 60 s (qualification)	2500	\ /m== =
V _{ISO}		t = 1 s (100% production)	3000	Vrms
R _S	Insulation resistance	$V_{IO} = 500 \text{ V at T}_{S}$	>10 ⁹	Ω
	Pollution degree		2	

⁽³⁾ Climatic Classification 40/125/21

Table 2. IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	sic isolation group Material group	
	Rated mains voltage ≤ 150 Vrms	I–IV
Installation classification	Rated mains voltage ≤ 300 Vrms	I–III
	Rated mains voltage ≤ 400 Vrms	I–II

⁽²⁾ Measured from input pin to ground.



REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice	Recognized under 1577 Component Recognition Program ⁽¹⁾
File number: pending (40016131)	File number: pending (1698195)	File number: pending (E181974)

⁽¹⁾ Production tested ≥ 3000 Vrms for 1 second in accordance with UL 1577.

LIFE EXPECTANCY vs WORKING VOLTAGE

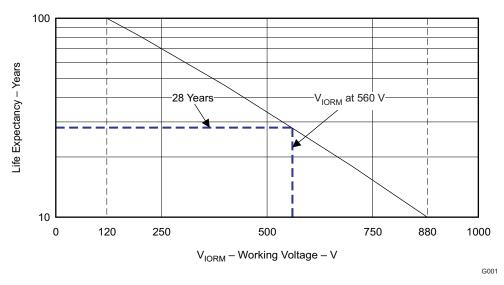


Figure 4. Life Expectancy vs Working Voltage

IEC SAFETY LIMITING VALUES

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER		TEST CONDITIONS		TYP	MAX	UNIT
	Safety input, output, or supply	$\theta_{JA} = 212$ °C/W, $V_I = 5.25$ V, $T_J = 150$ °C, $T_A = 25$ °C			112	A
IS	current	$\theta_{JA} = 212$ °C/W, $V_I = 3.45$ V, $T_J = 150$ °C, $T_A = 25$ °C			171	mA
T _S	Maximum case temperature				150	°C

The safety-limiting constraint is the absolute-maximum junction temperature specified in the *Absolute Maximum Ratings* table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the *Thermal Characteristics* table is that of a device installed in the JESD51-3, Low-Effective-Thermal-Conductivity Test Board for Leaded Surface-Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.



PACKAGE THERMAL CHARACTERISTICS

(over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
0	Junction-to-air thermal resistance	Low-K thermal resistance ⁽¹⁾		212		°C/W
θ_{JA}		High-K thermal resistance ⁽¹⁾		122		C/VV
θ_{JB}	Junction-to-board thermal resistance			37		°C/W
θ_{JC}	Junction-to-case thermal resistance			69.1		°C/W
P_D	Device power dissipation	$V_{CC1} = V_{CC2} = 5.5 \text{ V}, T_J = 150^{\circ}\text{C}, C_L = 15 \text{ pF},$ Input a 150-Mbps 50% duty-cycle square wave			390	mW

(1) Tested in accordance with the low-K or high-K thermal metric definitions of EIA/JESD51-3 for leaded surface-mount packages

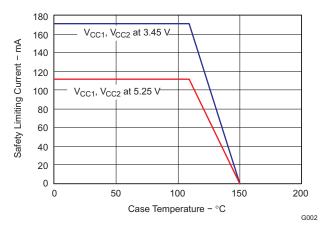


Figure 5. θ_{JC} Thermal Derating Curve per IEC 60747-5-2

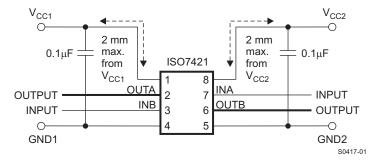


Figure 6. Typical ISO7421 Application Circuit



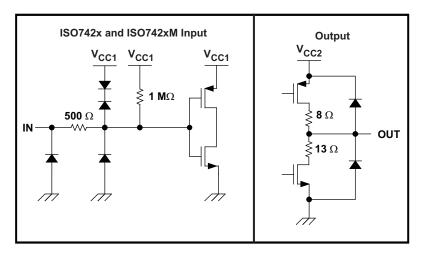
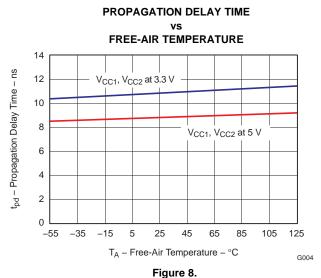


Figure 7. Device I/O Schematics



TYPICAL CHARACTERISTICS



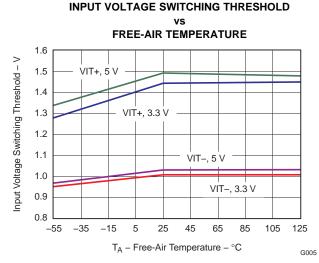


Figure 9.

FAIL-SAFE VOLTAGE THRESHOLD

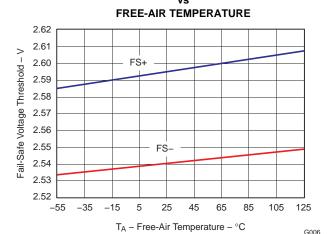


Figure 10.

HIGH-LEVEL OUTPUT CURRENT

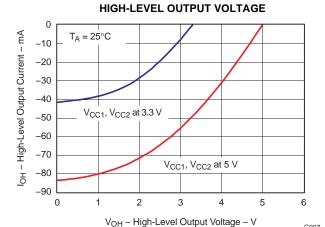


Figure 11.

LOW-LEVEL OUTPUT CURRENT LOW-LEVEL OUTPUT VOLTAGE

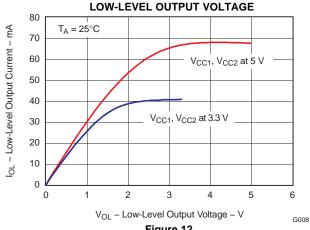


Figure 12.

G007

SLLS984D -JUNE 2009-REVISED JULY 2010



REVISION HISTORY

Cr	nanges from Original (June 2009) to Revision A	Page
•	Added devices ISO7420 and ISO7420M to the data sheet	1
•	Added the I _{CC} EQUATIONS section	
Cr	nanges from Revision A (December 2009) to Revision B	Page
•	Switching Characteristics Table, Added Note (2) - Typical specifications are measured at ideal conditions of 25°C. Max or Min specifications are measured at worst case conditions for V _{CC} and temperature	4
Cŀ	nanges from Revision B (February 2010) to Revision C	Page
•	Added devices ISO7420F and ISO7420FM to the data sheet	1
•	Added The suffix M indicates wide temperature range (–55°C to 125°C) and the suffix F indicates output-low option in fail-safe condition. All other devices without the F suffix default to output-high in fail-safe state.	1
•	Changed the Function Table Output values for PU (Open) From: H To: H/L	2
•	Changed the Function Table Output values for PU (X) From: H To: H/L	2
•	Changed the Function Table Output values for PU (X) From: H/L To: H	2
•	Added Note (2) in the Function Table	2
•	Added ISO7420F and ISO7420FM tothe Available Options Table	2
•	Changed value from a max of 4 mA to a min of -4 mA	3
•	Changed value from a min of -4 mA to a max of 4 mA	3
•	Changed Electrical Characteristics Conditions	4
•	Deleted C _i from the ELECTRICAL CHARACTERISTICS	
•	Added (All inputs switching with square wave clock signal for dynamic ICC measurement)	
•	Changed SWITCHING CHARACTERISTICS conditions	
•	Changed PWD parameter from duration to width	4
•	Changed ELECTRICAL CHARACTERISTICS conditions	
•	Added High-level output voltage ISO7420 / 7421 (3.3-V side) test condition	5
•	Changed High-level output voltage min value	
•	Deleted C _I specification	5
•	Added (All inputs switching with square wave clock signal for dynamic ICC measurement)	
•	Changed SWITCHING CHARACTERISTICS conditions	
•	Changed Pulse duration distortion to Pulse width distortion	
•	Changed ELECTRICAL CHARACTERISTICS conditions	
•	Added High-level output voltage ISO7420 / 7421 (5-V side) test condition	
•	Changed High-level output voltage min value	
•	Deleted C _I specification	
•	Added (All inputs switching with square wave clock signal for dynamic ICC measurement)	
•	Changed SWITCHING CHARACTERISTICS conditions	
•	Changed Pulse duration distortion to Pulse width distortion	
•	Changed ELECTRICAL CHARACTERISTICS conditions	
•	Deleted C _I specification	
•	Added (All inputs switching with square wave clock signal for dynamic ICC measurement)	
•	Changed SWITCHING CHARACTERISTICS conditions	
•	Changed Pulse duration distortion to Pulse width distortion	
•	Changed Note 1 Figure 1	



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•	Changed Figure 2	8
•	Added input to output and note 1 to Isolation resistance, input to output	9
•	Changed the Isolation resistance test conditions	9
•	Changed the Isolation resistance test conditions	9
•	Added note 1 to Barrier capacitance, input to output	9
•	Added Input capacitance	9
•	Changed $T_J = 170$ °C to $T_J = 150$ °C	10
•	Changed From: 124mA To: 107mA	10
•	Changed $T_J = 170$ °C to $T_J = 150$ °C	10
•	Changed From: 190mA To: 164mA	10
•	Changed Figure 5	11
•	Changed Figure 7	12
CI	nanges from Revision C (March 2010) to Revision D	Page
•	Deleted devices ISO7420F and ISO7420FM from the data sheet	1
•	Updated the Features List	1
•	Updated the device Description. Add paragraph - Note: The ISO7420 and ISO7421	1
•	Changed the Function Table Output values for PU (Open) From: H/L To: H	2
•	Changed ISO7420M T _A temp From: -55 to 125 To: 40 to 125 in the Available Options Table	2
•	Added Tstg to the Absolute Maximum Ratings Table	3
•	Updated the Recommended Opetating Conditions Table	3
•	Updates throughout the Electrical Characteristics and Switching Characteristics tables	4
•	Updated the Supply Current test conditions	4
•	Changed Figure 2	8
•	Changed Note 1 in Figure 3	<mark>8</mark>
•	Changed Minimum internal gap MIN value From: 0.008 To: 0.014mm	9
•	Changed the Barrier capacitance, input to output test conditions	9
•	Changed the Input capacitance test conditions	9
•	Changed the V _{IORM} , V _{PR} , and V _{IOTM} unit values From: V To: Vpeak	9
•	Changed V _I From: 5.5V To: 5.25V	10
•	Changed From: 107mA To: 112mA	10
•	Changed V _I From: 3.6V To: 3.45V	10
•	Changed From: 164mA To: 171mA	
•	Changed Figure 5	
•	Deleted the I _{CC} EQUATIONS section	
•	Changed Figure 7	
•	Deleted the SUPPLY CURRENT vs SIGNAL RATE (ALL CHANNELS) graphs and the EYE DIAGRAM plots	
_		

PACKAGE OPTION ADDENDUM

www.ti.com 17-May-2010

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
ISO7420D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO7420DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO7420MD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO7420MDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO7421D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO7421DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO7421MD	PREVIEW	SOIC	D	8	75	TBD	Call TI	Call TI
ISO7421MDR	PREVIEW	SOIC	D	8	2500	TBD	Call TI	Call TI

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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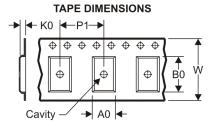
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PACKAGE MATERIALS INFORMATION

www.ti.com 20-Jul-2010

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7420DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7420MDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7421DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 20-Jul-2010

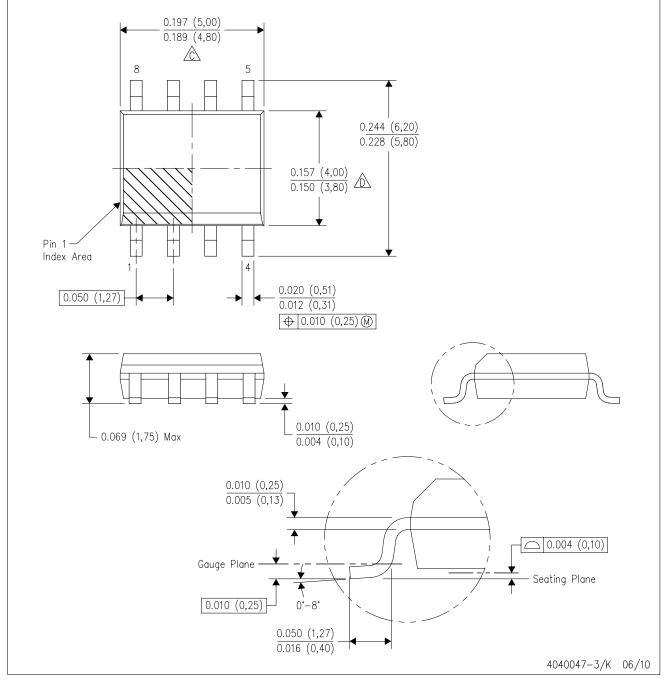


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7420DR	SOIC	D	8	2500	358.0	335.0	35.0
ISO7420MDR	SOIC	D	8	2500	358.0	335.0	35.0
ISO7421DR	SOIC	D	8	2500	358.0	335.0	35.0

D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



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